

Data Sheet January 2000 File Number 3409.3

# 30A, 1200V Hyperfast Diode

The RHRP30120 is a hyperfast diode with soft recovery characteristics ( $t_{rr}$  < 65ns).lt has half the recovery time of ultrafast diodes and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of high frequency switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, reducing power loss in the switching transistors.

Formerly developmental type TA49041.

## **Ordering Information**

PART NUMBER	PACKAGE	BRAND	
RHRP30120	TO-220AC	RHR30120	

NOTE: When ordering, use the entire part number.

# Symbol



#### **Features**

	Hyperfast with Soft Recovery	
•	Operating Temperature	75°C
•	Reverse Voltage	200V

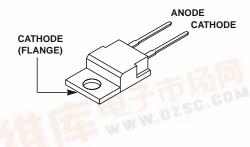
- Avalanche Energy Rated
- Planar Construction

### **Applications**

- Switching Power Supplies
- · Power Switching Circuits
- General Purpose

### **Packaging**

JEDEC TO-220AC



# Absolute Maximum Ratings $T_C = 25^{\circ}C$

	RHRP30120	UNITS
Peak Repetitive Reverse VoltageVRRM	1200	V
Working Peak Reverse Voltage	1200	V
DC Blocking Voltage	1200	V
Average Rectified Forward Current	30	Α
$(T_C = 78^{\circ}C)$		
Repetitive Peak Surge Current	60	Α
(Square Wave, 20kHz)		
(Square Wave, 20kHz)  Nonrepetitive Peak Surge CurrentIFSM	300	Α
(Halfwave, 1 Phase, 60Hz)		
Maximum Power Dissipation	125	W
Avalanche Energy (See Figures 7 and 8)	30	mJ
Operating and Storage Temperature	-65 to 175	°C



 $\textbf{Electrical Specifications} \hspace{0.5cm} \textbf{T}_{C} = 25^{o}\text{C}, \hspace{0.1cm} \textbf{Unless Otherwise Specified}$ 

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V <sub>F</sub>	I <sub>F</sub> = 30A	-	-	3.2	V
	I <sub>F</sub> = 30A, T <sub>C</sub> = 150°C	-	-	2.6	V
I <sub>R</sub>	V <sub>R</sub> = 1200V	-	-	250	μΑ
	V <sub>R</sub> = 1200V, T <sub>C</sub> = 150 <sup>o</sup> C	-	-	1	mA
t <sub>rr</sub>	I <sub>F</sub> = 1A, dI <sub>F</sub> /dt = 100A/μs	-	-	65	ns
	$I_F = 30A$ , $dI_F/dt = 100A/\mu s$	-	-	75	ns
ta	I <sub>F</sub> = 30A, dI <sub>F</sub> /dt = 100A/μs	-	48	-	ns
t <sub>b</sub>	I <sub>F</sub> = 30A, dI <sub>F</sub> /dt = 100A/μs	-	22	-	ns
$R_{ heta JC}$		-	-	1.2	oC/W

#### **DEFINITIONS**

 $V_F$  = Instantaneous forward voltage (pw = 300 $\mu$ s, D = 2%).

I<sub>R</sub> = Instantaneous reverse current.

 $t_{rr}$  = Reverse recovery time (See Figure 6), summation of  $t_a$  +  $t_b$ .

t<sub>a</sub> = Time to reach peak reverse current (See Figure 6).

 $t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 6).

 $R_{\theta JC}$  = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

# **Typical Performance Curves**

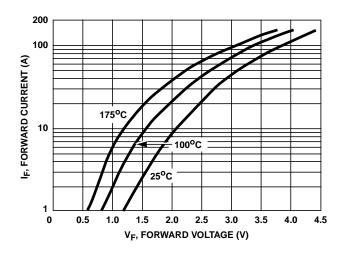


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

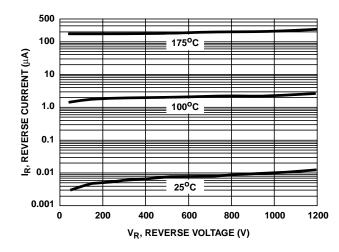


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

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### Typical Performance Curves (Continued)

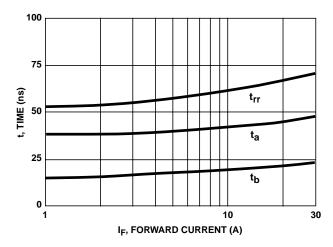


FIGURE 3. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT

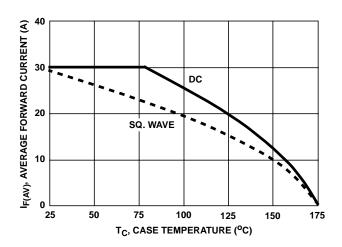


FIGURE 4. CURRENT DERATING CURVE

#### Test Circuits and Waveforms

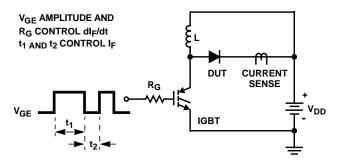


FIGURE 5. t<sub>rr</sub> TEST CIRCUIT

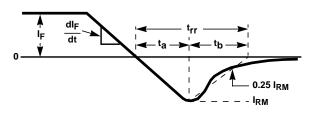


FIGURE 6. t<sub>rr</sub> WAVEFORMS AND DEFINITIONS

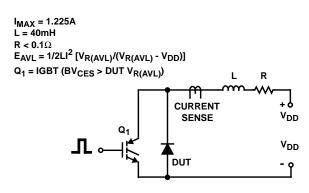


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

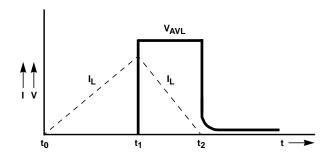


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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